



2BF1,2BF3,2BF5

GLASS PASSIVATED SILICON ULTRAFAST RECOVERY DIODE

Features:

1. Silicon diffusion mesa.
2. Glass Passivated package.
3. Small volume, light weight.
4. Small high-temperature leakage.
5. Good thermal stability.
6. High reliability.
7. Implementation of standards: GJB33A-97, QZJ840611A, QZJ840611



TECHNICAL DATA:

($T_a = 25^\circ\text{C}$)

Parameter name	Symbols	Unit	Specifications			Test Condition		
			2BF1	2BF3	2BF5	2BF1	2BF3	2BF5
Use for	Ultra-high-frequency,switch circuit.							
Store temperature	T	$^\circ\text{C}$	-55~+150					
Quality Class	JP, JT, JCT, GS, G, G+							
Peak Repetitive Reverse Voltage	V_{RRM}	V	50~800					
Average Forward Current	$I_{F(AV)}$	A	1.0	3.0	5.0			
Peak Forward Voltage	V_{FM}	V	A~E:2.2 F~G:2.5	A~C:2.4 D~G:2.8		$I=I_{F(AV)}$	$I=A I_{F(AV)}$ A=3.1415926	$I=I_{F(AV)}$
Average Forward Voltage	V_F	V	A~E:0.9 F~G:1.0	A~C:1.2 D~G:1.4		$I=I_{F(AV)}$		
Non-repeat Forward Surge Current	I_{FSM}	A	30	50	60	Single-phase industrial frequency sine half wave 10ms		
Peak Reverse Current	I_{RM1}	μA	10			$V_R=V_{RRM}, T_a=25^\circ\text{C}$		
Peak Reverse Current	I_{RM2}	μA	200			$V_R=V_{RRM}, T_a=125^\circ\text{C}$		
Junction Temperature	T_{jm}	$^\circ\text{C}$	125					
Reverse Recovery Time	t_{rr}	μS	A~E:0.1 F~G:0.2			$V_R=10\text{V}, I_F=50\text{mA}, R_L=75\text{ohms}$		

SPECIFICATIONS:

A	B	C	D	E	F	G
50V	100V	200V	300V	400V	600V	800V

Outline and Dimensions:

Model cross: 2BF5(2CK105,BZK5)